

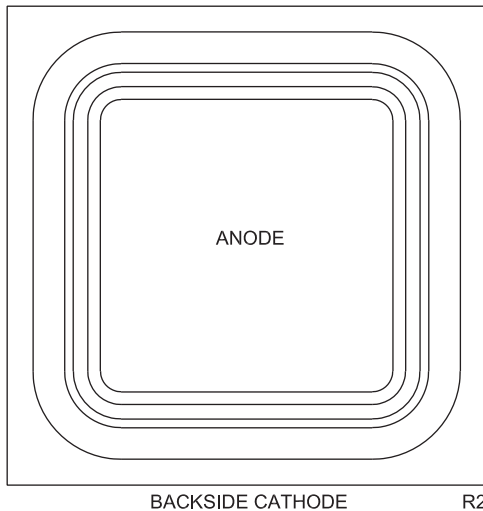
PROCESS CPD96V
Schottky Diode
500mA Low V_F Schottky Diode Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	20 x 20 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	16.4 x 16.4 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

28,028

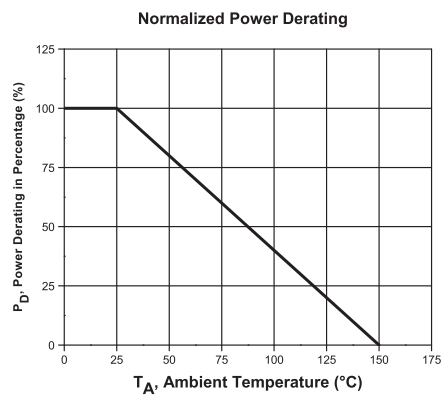
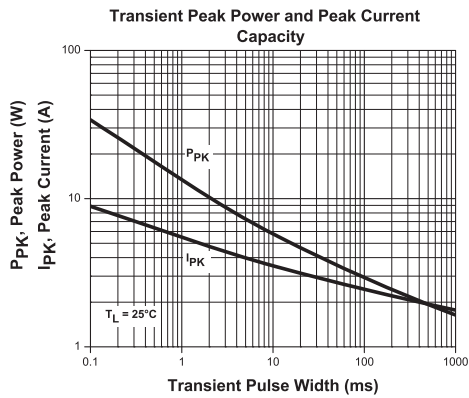
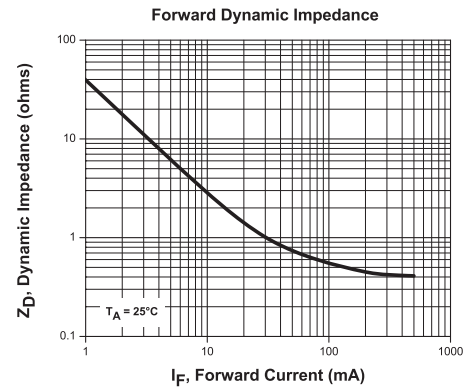
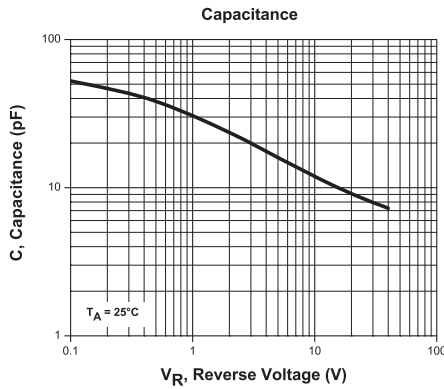
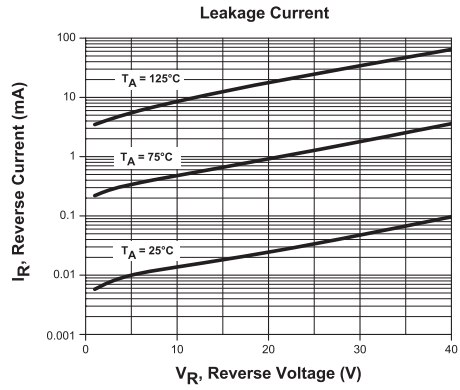
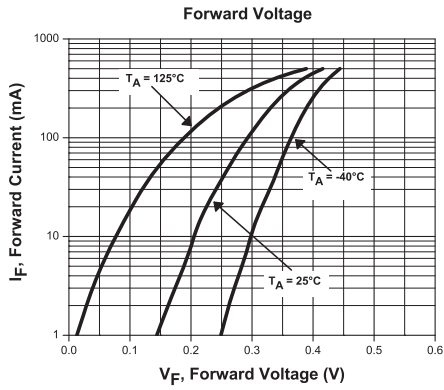
PRINCIPAL DEVICE TYPES

CMLSH05-4

R5 (22-March 2010)

PROCESS CPD96V

Typical Electrical Characteristics



R5 (22-March 2010)